

Silicon NPN Power Transistors 2SC2336 2SC2336A 2SC2336B

DESCRIPTION

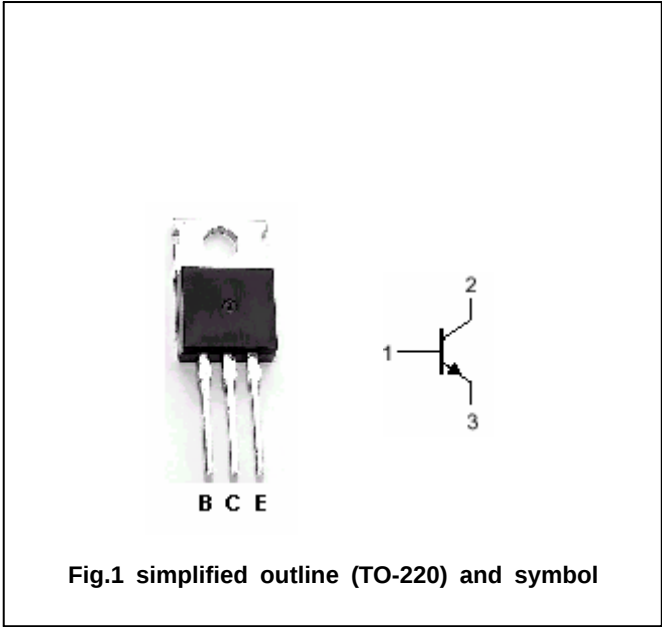
- With TO-220 package
- Complement to type 2SA1006, 2SA1006A,2SA1006B

APPLICATIONS

- Audio frequency power amplifier
- High frequency power amplifier

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	180	V
			200	
			250	
V _{CEO}	Collector-emitter voltage	Open base	180	V
			200	
			250	
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		1.5	A
I _{CM}	Collector current-peak		3.0	A
P _T	Total power dissipation	T _a =25	1.5	W
		T _C =25	25	
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

Silicon NPN Power Transistors**2SC2336 2SC2336A 2SC2336B****CHARACTERISTICS**

Tj=25 unless otherwise specified

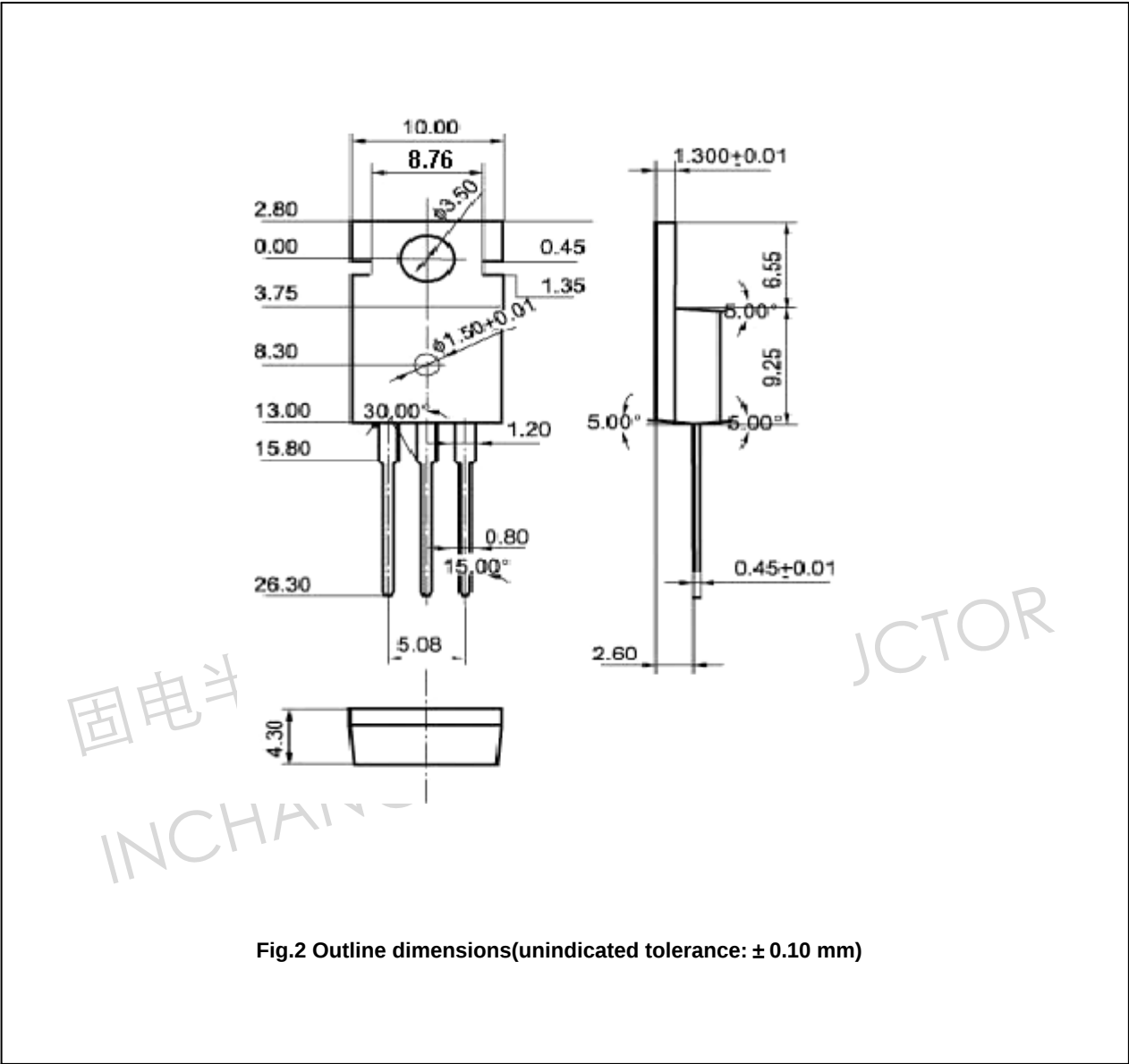
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CEsat}	Collector-emitter saturation voltage	$I_C=0.5A; I_B=50mA$			1.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=0.5A; I_B=50mA$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=150V; I_E=0$			1	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=3V; I_C=0$			1	μA
h_{FE-1}	DC current gain	$I_C=5mA; V_{CE}=5V$	30			
h_{FE-2}	DC current gain	$I_C=150mA; V_{CE}=5V$	60		320	
C_{ob}	Output capacitance	$I_E=0; V_{CB}=10V, f=1MHz$		30		pF
f_T	Transition frequency	$I_C=100mA; V_{CE}=10V$		95		MHz

◆ **h_{FE-2} Classifications**

R	Q	P
60-120	100-200	160-320

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PACKAGE OUTLINE



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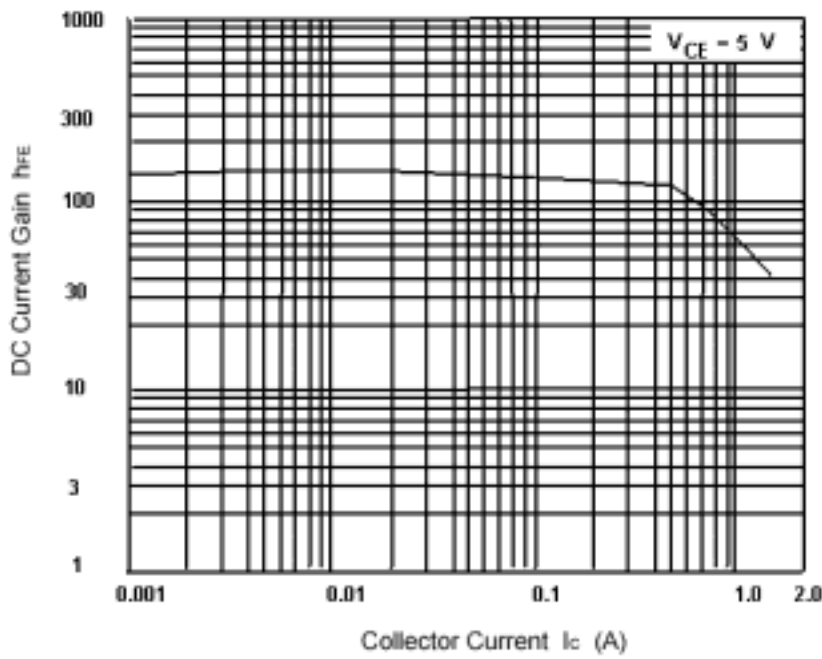


Fig.3 DC current Gain

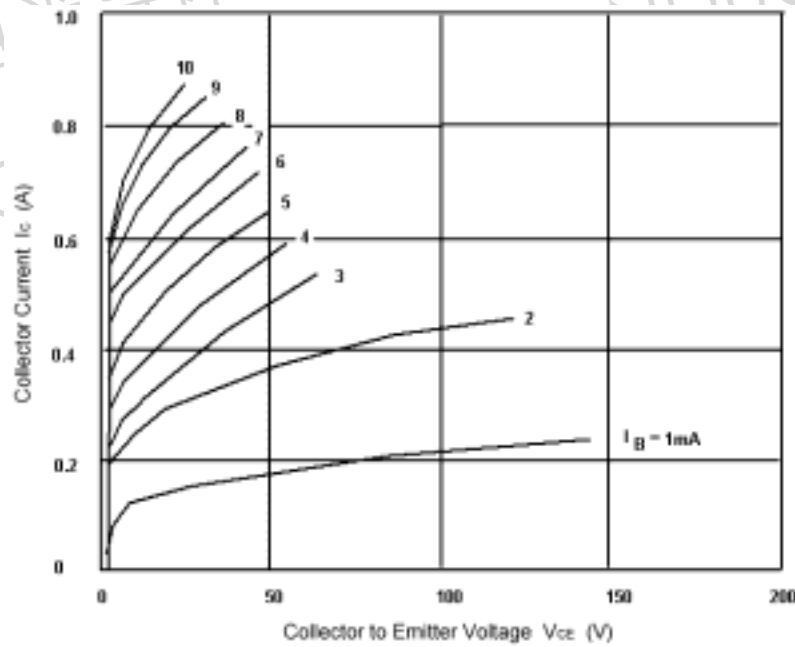


Fig.4 Static Characteristic

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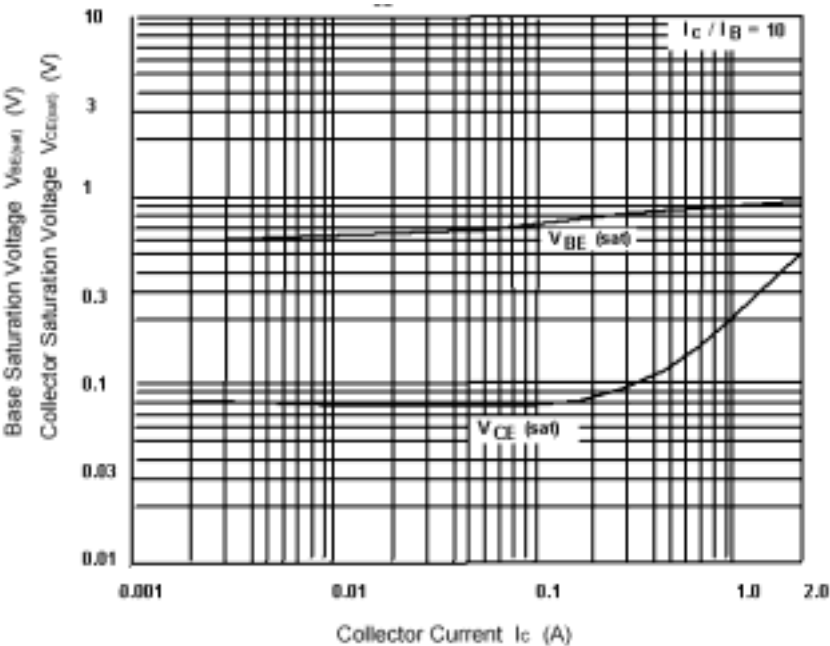


Fig.5 Base-Emitter Saturation Voltage
Collector-Emmitter Saturation Voltage

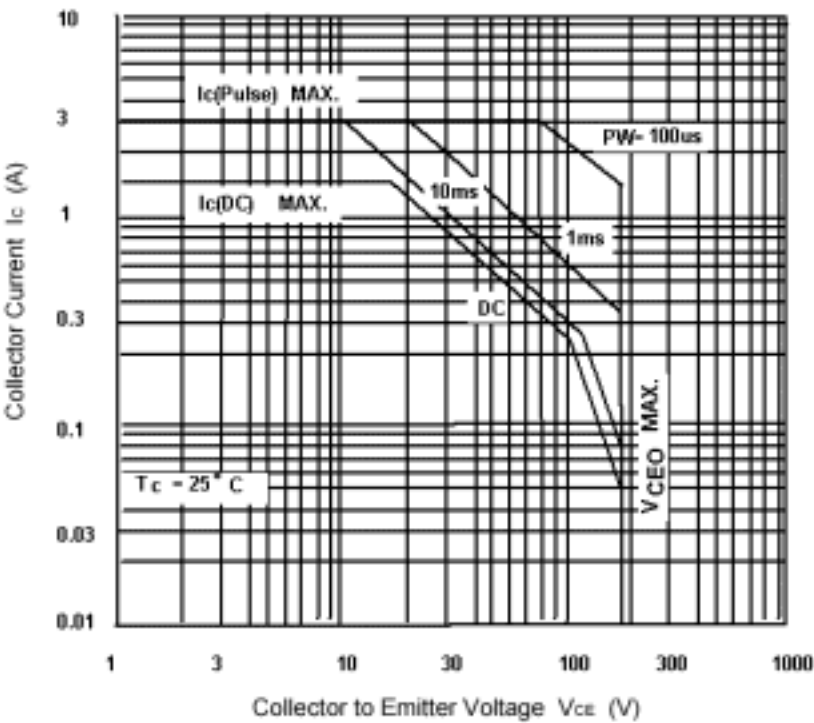


Fig.6 Safe Operating Area